

TITLE OF THE INVENTION:

PROCESSING OF SEMICONDUCTOR SUBSTRATES WITH DENSE FLUIDS
COMPRISING ACETYLENIC DIOLS AND/OR ALCOHOLS

BACKGROUND OF THE INVENTION

[0001] Small quantities of contaminants are detrimental to the microchip fabrication process in the manufacturing of semiconductor electronic components. Contaminants may be introduced into the component from many sources such as residues from
5 manufacturing process steps such as lithography, etching, stripping, and chemical mechanical planarization (CMP); particulates either indigenous to and/or resulting from manufacturing processes; inorganic particulates or materials such as native or chemical oxides, metal-containing compounds; or other sources. Contaminants, in the form of particulates, films, or molecules, can cause a variety of defects, such as short circuits,
10 open circuits, and silicon crystal stacking faults. These defects can cause the failure of the finished component, such as microelectronic circuits, and these failures can cause significant yield reductions, which greatly increases manufacturing costs.

[0002] Microelectronic circuit fabrication requires many processing steps. Processing is performed under extremely clean conditions and the amount of contamination needed
15 to cause fatal defects in microcircuits is extremely small. For example, an individual particle as small as 0.01 micrometer in size can result in a killer defect in a modern microcircuit. Microcontamination may occur at any time during the many steps needed to complete the microcircuit. Therefore, periodic cleaning of the wafers used for microelectronic circuits is needed to maintain economical yields. Also, tight control of
20 purity and cleanliness of the processing materials is required.

[0003] Cleaning is the most frequently repeated step in the manufacture of microelectronic circuits. At the 0.18-micrometer design rule, 80 of the approximately 400 total processing steps are cleaning steps. Wafers typically are cleaned after every contaminating process step and before each high temperature operation to ensure the quality of the circuit. Exemplary cleaning and removal applications include photoresist stripping/removal, particle/residue removal for post-chemical mechanical planarization (post-CMP cleaning), particle/residue removal for post-dielectric etching (or post-metal etching), and removal of metal contaminants.

[0004] Numerous cleaning methods have been used in the manufacture of semiconductor electronic components. These include immersion in liquid cleaning agents to remove contamination through dissolution and chemical reaction. Such immersion may also serve to reduce the van der Waals adhesive forces and introduce double layer repulsion forces, thereby promoting the release of insoluble particles from surfaces. A standard wet cleaning process in common use begins with exposure to a mixture of H_2SO_4 , H_2O_2 , and H_2O at 110-130°C, and is followed by immersion in HF or dilute HF at 20-25°C. Next, a mixture of NH_4OH , H_2O_2 , and H_2O at 60-80°C removes particles and then a mixture of HCl , H_2O_2 , and H_2O at 60-80°C removes metal contamination. Each of these steps is followed by a high purity H_2O rinse. This wet cleaning process reaches fundamental barriers at dimensions less than 0.10 micrometer. As the device geometries shrink and gate oxide thickness decreases, sub-micrometer particle removal becomes increasingly difficult.

[0005] Stripping/removal of primarily organic photoresist may be performed using dilute aqueous mixtures containing H_2SO_4 and H_2O_2 . Alternatively, the stripping/removal may be performed using a two-step plasma, or reactive ion etching (RIE) process, followed by wet chemical cleaning of the residue material. Ozonated H_2O has been used for the decomposition of hydrocarbon surface contaminants on silicon wafers.

[0006] Brush scrubbing has been used to enhance the liquid immersion process by introducing hydrodynamic shear forces to the contaminated surfaces. A typical application uses a wafer cleaning apparatus comprising two opposed brushes for brushing a vertically disposed wafer in a tank that can contain a process liquid.

- 5 **[0007]** The addition of ultrasonic energy can increase the effectiveness of the liquid immersion process. Sound waves vibrating at frequencies greater than 20,000 cycles per second (20 KHz), i.e., beyond the range of human hearing, have been used to transmit high frequency energy into liquid cleaning solutions.

- [0008]** Wet processing methods may become problematic as microelectronic circuit dimensions decrease and as environmental restrictions increase. Among the limitations of wet processing are the progressive contamination of re-circulated liquids, re-deposition from contaminated chemicals, special disposal requirements, environmental damage, special safety procedures during handling, reduced effectiveness in deeply patterned surfaces due to surface tension effects and image collapse (topography sensitivity), dependence of cleaning effectiveness on surface wet-ability to prevent re-adhesion of contaminants, and possible liquid residue causing adhesion of remaining particles. Aqueous cleaning agents that depend upon chemical reaction with surface contaminants may also present compatibility problems with new thin film materials or with more corrosion-prone metals such as copper. Further, aqueous cleaning agents may introduce hydroxyl groups in porous low and ultralow dielectric constant materials, which may increase the dielectric constant of the material. In addition, the International Technology Roadmap for Semiconductors has recommended a 62% reduction in water use by the year 2005 and an 84% reduction by the year 2014 to prevent water shortages. With the continuing trend toward increasing wafer diameters having a larger precision surface area, larger volumes of liquid chemicals will be required in the fabrication process.
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- 25

[0009] In view of these problems, methods for dry (anhydrous) surface cleaning of semiconductor electronic components are being developed. Among these is gas jet cleaning to remove relatively large particles from silicon wafers. However, gas jets can be ineffective for removing particles smaller than about 5 micrometers in diameter

5 because the forces that hold particles on the surface are proportional to the particle size, while the aerodynamic drag forces generated by the flowing gas for removing the particles are proportional to the particle diameter squared. Therefore, the ratio of these forces tends to favor adhesion as the particle size shrinks. In addition, smaller particles are not exposed to strong drag forces in the jet since they normally lie within the surface

10 boundary layer where the gas velocity is low.

[0010] Exposure to ozone combined with ultraviolet light can be used to decompose contaminating hydrocarbons from surfaces, but this technique has not been shown to remove inorganic contaminants or particles effectively.

[0011] Other alternatives to wet cleaning include the use of jets containing snow or pellet projectiles comprising frozen Ar, N₂, H₂O or CO₂, which are used to “sandblast” contaminated surfaces. In these processes, pressurized gaseous or gas/liquid mixtures are expanded in a nozzle to a pressure near or below atmospheric pressure. The resulting Joule-Thomson cooling forms solid or liquid aerosol particles, which traverse the boundary layer and strike the contaminated surface. This technique requires

15 extremely clean and pure processing materials. Trace molecular contaminants (e.g., hydrocarbons) in the feed gases can condense into solid particulates or droplets upon expansion, causing deposition of new contaminants on the surface. Although useful in providing removal of many surface contaminants, these processes cannot remove all of the important contaminants present on a wafer surface, and have not yet found wide

20 acceptance in the semiconductor industry.

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[0012] Immersion in supercritical fluids is another alternative to wet cleaning. The effectiveness of supercritical fluids in various cleaning and extraction applications is well established and extensively documented. The solvency of supercritical fluids is much greater than the corresponding gaseous state; thus, supercritical fluids can effectively
5 dissolve and remove unwanted films and molecular contaminants from a precision surface. The contaminants can be separated from the cleaning agent by a reduction in pressure below the critical value, which concentrates the contaminants for disposal and permits recovery and re-use of the cleaning fluid.

[0013] Supercritical CO₂ in particular has been used as a versatile and cost effective
10 method to overcome the above-mentioned problems in wafer cleaning. Supercritical CO₂ effectively cleans parts with increasingly smaller dimensions and lowers water usage, thereby yielding improvements in performance and environmental benefits. Preliminary Cost of Ownership (CoO) studies have shown that supercritical CO₂ cleaning is also more cost effective when compared to aqueous cleaning. However, while
15 liquid/supercritical CO₂ by itself may be capable of dissolving primarily non-polar species, monomers and low molecular weight organic polymers, other species such as inorganic and/or polar compounds and high molecular weight polymers are not easily dissolved in either liquid or supercritical CO₂. To remedy this lack of solvency, entrainers such as co-solvents and surfactants are added to the liquid or supercritical CO₂ to increase
20 contaminant solubility and thereby widen the range of contaminants that can be removed.

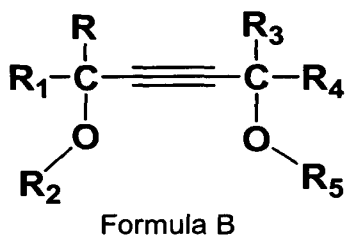
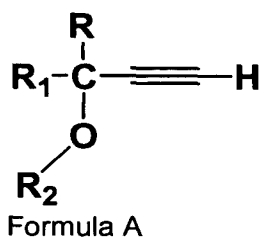
[0014] A wide variety of cosolvents, chelating agents and surfactants have been used/proposed for use with CO₂ for semiconductor substrate cleaning. These include specific esters, ethers, alcohols, glycols, ketones, amines, amides, carbonates,
25 carboxylic acids, alkane diols, alkanes, hydrogen peroxide, and chelating agents. Fluorinated and silicone-based surfactants have traditionally been used with liquid or

supercritical CO₂ for wafer cleaning applications because of their high solubility in CO₂. These surfactants, however, are generally expensive and may increase overall processing costs.

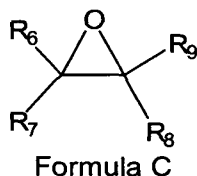
[0015] Future microcircuits will have smaller feature sizes and greater complexities, and will require more processing steps in their fabrication. Contamination control in the process materials systems and processing environment will become even more critical. In view of these anticipated developments, there is a need for improved wafer cleaning methods to maintain or improve economical yields in the manufacture of these smaller and more complex microelectronic systems. In addition, the advent of smaller feature sizes and greater complexities will require improved fabrication processes steps including etching, thin film deposition, planarization, and photoresist development. Embodiments of the present invention, which are described below and defined by the following claims, address this need by improved processing methods utilizing dense cleaning fluids comprising lower cost, acetylenic alcohol or acetylenic diol entrainers and/or nitriles.

BRIEF SUMMARY OF THE INVENTION

[0016] The present invention provides a dense cleaning fluid for removing contaminants from a substrate and a method comprising same. In one aspect of the present invention, there is provided a dense cleaning fluid comprising: a dense fluid and at least one acetylenic diol or acetylenic alcohol represented by the following formulas A or B:



wherein R, R₁, R₃, and R₄ are independently a hydrogen atom, a linear alkyl group comprised of from 1 to 34 carbon atoms, a branched alkyl group comprised of from 2 to 34 carbon atoms, and R₂ and R₅ are each independently a hydrogen atom; a hydroxyl terminated poly(alkylene oxide) chain derived from 1 to 30 alkylene oxide monomer units of the following Formula C:



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wherein R₆, R₇, R₈, and R₉ are independently a hydrogen atom, a linear alkyl group comprised of from 1 to 5 carbon atoms, a branched alkyl group comprised of from 2 to 5 carbon atoms, or a cyclic alkyl group comprised of from 3 to 5 carbon atoms; an interactive functional group; and combinations thereof.

15 **[0017]** In another aspect of the present invention, there is provided a dense cleaning fluid comprising: a dense fluid, at least one acetylenic diol or acetylenic alcohol represented by the aforementioned Formulas A or B; and at least one entrainer selected from the group consisting of a co-solvent, a surfactant, a chelating agent, and combinations thereof.

20 **[0018]** In a further aspect of the present invention, there is provided a dense cleaning fluid for removing contaminants from a substrate comprising: from 20 to 99 weight percent of a dense fluid; from 1 to 20 weight percent of at least one acetylenic alcohol or acetylenic diol represented by the aforementioned Formulas A or B; 0 to 40 weight

percent of at least one cosolvent; and 0 to 20 weight percent of at least one chelating agent.

[0019] In yet another aspect of the present invention, there is provided a dense cleaning fluid for removing contaminants from a substrate comprising: a dense fluid and
5 at least one derivatized acetylenic alcohol or derivatized acetylenic wherein the derivatized alcohol or the derivatized diol comprises at least one interactive functional group selected from the group consisting of an amine and acid functional group; an ester functional group; an ether and alcohol functional group; an ester and alcohol functional group; a nitrile functional group; a carbonate functional group; and combinations thereof.

10 **[0020]** In a still further aspect of the present invention, there is provided a method for removing contaminants from a substrate comprising: contacting the substrate with a dense cleaning fluid comprising a dense fluid and at least one acetylenic diol or acetylenic alcohol represented by the aforementioned Formulas A or B.

[0021] In another aspect of the present invention, there is provided a method a method
15 for removing contaminants from a substrate comprising: introducing the substrate comprising contaminants into a processing chamber; contacting the substrate with a dense cleaning fluid comprising a dense fluid and at least one entrainer selected from the group consisting of an acetylenic alcohol, an acetylenic diol, a derivatized acetylenic alcohol, a derivatized acetylenic diol, a cosolvent, a chelating agent, a surfactant, and
20 combinations thereof to provide a spent dense fluid and a treated substrate; and separating the contaminants and the at least one entrainer from the spent dense fluid.

[0022] These and other aspects of the present invention are provided in the Detailed Description of the Invention.

BRIEF DESCRIPTION OF SEVERAL VIEWS OF THE DRAWINGS

[0023] Figure 1 is a pressure-temperature phase diagram for a single component supercritical fluid.

[0024] Figure 2 is a density-temperature phase diagram for CO₂.

5 **[0025]** Figure 3 is a generalized density-temperature phase diagram.

[0026] Figure 4 is a process flow diagram illustrating an embodiment of the invention.

DETAILED DESCRIPTION OF THE INVENTION

[0027] Dense fluids, particularly supercritical fluids, are well suited to convey
10 processing agents to substrates such as microelectronic components undergoing processing steps and for removing undesirable contaminants from the microelectronic components upon completion of various process steps. These process steps typically are carried out batchwise and may include cleaning, film stripping, etching, deposition, drying, and planarization. Other uses for supercritical fluids include precipitation of nano-
15 particles and suspension of metallic nano-crystals. It is envisioned that the dense cleaning fluids of the present invention may replace aqueous and organic-solvent based formulations that have traditionally been used to remove organic, inorganic and metallic residue from a substrate, and prepare the substrate for further processing.

[0028] A wide variety of contamination-sensitive substrates encountered in the
20 fabrication of microelectronic devices and micro-electromechanical devices can be cleaned or processed using embodiments of the present invention. The term "substrate" as used herein means any article of manufacture that can be contacted with a dense fluid or a dense cleaning fluid. Such substrates may include, for example, silicon or gallium arsenide wafers, reticles, photomasks, flat panel displays, internal surfaces of
25 processing chambers, printed circuit boards, surface mounted assemblies, electronic assemblies, sensitive wafer processing system components, electro-optical, laser and

spacecraft hardware, surface micro-machined systems, and other related substrates subject to contamination during fabrication. Typical contaminants to be removed from these substrates in a cleaning process may include, for example, organic compounds such as exposed photoresist material, photoresist residue, UV- or X-ray-hardened photoresist, C-F-containing polymers, low and high molecular weight polymers, and other organic etch residues; inorganic compounds such as metal oxides, ceramic particles from CMP slurries and other inorganic etch residues; metal containing compounds such as organometallic residues and metal organic compounds; ionic and neutral, light and heavy inorganic (metal) species, moisture, and insoluble materials, including post-planarization particles.

[0029] The term "processing" or "processed" as used herein means contacting a substrate with a dense fluid or a dense cleaning fluid to effect physical and/or chemical changes to the substrate. The term "processing" may include, for example, film stripping, cleaning, drying, etching, planarization, deposition, extraction, photoresist development, or formation of suspended nano-particles and nano-crystals.

[0030] Dense fluids are ideal for removal of contaminants, particularly in microelectronic applications, because these fluids characteristically have high solvent power, low viscosity, high diffusivity, and negligible surface tension relative to the substrates being processed. As pointed out above, the processing fluids used in microelectronic processing preferably have high purity, much higher than that of similar fluids used in other applications to avoid further introduction of contaminants. The purification of extremely high purity fluids for these applications must be done with great care.

[0031] Figure 1 is a pressure-temperature phase diagram for a single component supercritical fluid. Referring to Figure 1, four distinct regions or phases, solid 1', liquid 2', gas 3' and supercritical fluid 4', exist for a single component. The critical point,

designated "C" in Figure 1, is defined as that pressure (critical pressure P_c) and temperature (critical temperature T_c) below which a single component can exist in vapor/liquid equilibrium. The density of the single component at the critical point is its critical density. Also shown in Figure 1 are the sublimation curve 5', or the line between "A" and "T" which separates the solid 1' and gas 3' regions, the fusion curve 6', or the line between "T" and "B" which separates the liquid 2' and solid 1' regions, and the vaporization curve 7', or the line between "T" and "C" which separates the liquid 2' and gas 3' regions. The three curves meet at the triple point, designated "T", wherein the three phases, or solid, liquid and gas, coexist in equilibrium.

10 **[0032]** A phase is generally considered a liquid if it can be vaporized by reducing pressure at constant temperature. Similarly, a phase is considered a gas if it can be condensed by reducing the temperature at a constant pressure. The gas and liquid regions become indistinguishable at or above the critical point C, as shown in Figure 1. Thus, a single-component supercritical fluid is defined as a fluid at or above its critical

15 temperature and pressure. A related single-component fluid having similar properties to a supercritical fluid is a single-phase fluid, which exists at a temperature below its critical temperature and a pressure above its liquid saturation pressure. A single-component subcritical fluid is defined as a fluid at a temperature below its critical temperature or a pressure below its critical pressure. In the present disclosure, the term "dense fluid" as

20 applied to a single-component fluid is defined to include a supercritical fluid, a single-phase fluid which exists at a temperature below its critical temperature and a pressure above its saturation pressure, and a single-component subcritical fluid. A single-component dense fluid also can be defined as a single-phase fluid at a pressure above its critical pressure or a pressure above its liquid saturation pressure. The term

25 "component" as used herein means an element (for example, hydrogen, helium, oxygen,

nitrogen) or a compound (for example, carbon dioxide, methane, nitrous oxide, sulfur hexafluoride).

[0033] An example of a dense fluid for a single component is illustrated in Figure 2, which is a representative density-temperature phase diagram for carbon dioxide. This diagram shows saturated liquid curve 1 and saturated vapor curve 3, which merge at critical point 5 at the critical temperature of 87.9°F (31.1°C) and critical pressure of 1,071 psia. Lines of constant pressure (isobars) are shown, including the critical isobar of 1,071 psia. Line 7 is the melting curve. The region to the left of and enclosed by saturated liquid curve 1 and saturated vapor curve 3 is a two-phase vapor-liquid region. The region outside and to the right of saturated liquid curve 1, saturated vapor curve 3, and melting curve 7 is a single-phase fluid region. The dense fluid as defined herein is indicated by cross-hatched regions 9 (at or above critical pressure) and 10 (below critical pressure).

[0034] A generic density-temperature diagram can be defined in terms of reduced temperature, reduced pressure, and reduced density as shown in Figure 3. The reduced temperature (T_R) is defined as the absolute temperature divided by the absolute critical temperature, reduced pressure (P_R) is defined as the absolute pressure divided by the absolute critical pressure, and reduced density (ρ_R) is defined as the density divided by the critical density (ρ_C). The reduced temperature, reduced pressure, and reduced density are all equal to 1 at the critical point by definition. Figure 3 shows analogous features to Figure 2, including saturated liquid curve 201 and saturated vapor curve 203, which merge at the critical point 205 at a reduced temperature of 1, a reduced density of 1, and a reduced pressure of 1. Lines of constant pressure (isobars) are shown, including critical isobar 207 for which $P_R = 1$. In Figure 3, the region to the left of and enclosed by saturated liquid curve 201 and saturated vapor curve 203 is the two-phase vapor-liquid region. The crosshatched region 209 above the $P_R = 1$ isobar and to the

right of the critical temperature $T_R = 1$ is a single-phase supercritical fluid region. The crosshatched region 211 above saturated liquid curve 201 and to the left of the critical temperature $T_R = 1$ is a single-phase compressed liquid region. The cross-hatched region 213 to the right of saturated vapor curve 203, and below the isobar $P_R = 1$

5 represents a single-phase compressed or dense gas. The dense fluid as defined herein includes the single-phase supercritical fluid region 209, single-phase compressed liquid region 211, and the single-phase dense gas region 213.

[0035] A dense fluid alternatively may comprise a mixture of two or more components. In this case, the dense fluid is defined as a single-phase multi-component fluid of a given
10 composition which is above its saturation or bubble point pressure, or which has a combination of pressure and temperature above the mixture critical point. The critical point for a multi-component fluid is defined as the combination of pressure and temperature above, which the fluid of a given composition exists only as a single phase. In the present disclosure, the term "dense fluid" as applied to a multi-component fluid is
15 defined to include both a supercritical fluid and a single-phase fluid that exists at a temperature below its critical temperature and a pressure above its bubble point or saturation pressure. A multi-component dense fluid also can be defined as a single-phase multi-component fluid at a pressure above its critical pressure or a pressure above its bubble point or liquid saturation pressure. A multi-component dense fluid differs from
20 a single-component dense fluid in that the liquid saturation pressure, critical pressure, and critical temperature are functions of composition.

[0036] A multi-component subcritical fluid is defined as a multi-component fluid of a given composition which has a combination of pressure and temperature below the mixture critical point.

25 **[0037]** The generic definition of a dense fluid thus includes a single component dense fluid as defined above as well as a multi-component dense fluid as defined above.

Similarly, a subcritical fluid may be a single-component fluid or a multi-component fluid.

In some embodiments, a single-component subcritical fluid or a multi-component subcritical fluid may be a dense fluid.

[0038] Depending upon the application, the dense fluid may be either a single-

5 component fluid or a multi-component fluid, and may have a reduced temperature in the range of about 0.2 to about 2.0, and a reduced pressure above 0.75. The reduced temperature is defined here as the absolute temperature of the fluid divided by the absolute critical temperature of the fluid, and the reduced pressure is defined here as the absolute pressure divided by the absolute critical pressure.

10 **[0039]** When carbon dioxide is used for a single-component dense cleaning fluid, the carbon dioxide may be heated to a temperature between about 86°F (30.08°C) and about 500°F (260°C) to generate the desired dense fluid pressure in the pressurization vessel. More generally, when using any component or components for the dense fluid, the fluid may be heated to a reduced temperature in the pressurization vessel of up to
15 about 2.0, wherein the reduced temperature is defined as the average absolute temperature of the fluid in the pressurization vessel after heating divided by the absolute critical temperature of the fluid. The critical temperature is defined for a fluid containing any number of components as that temperature above which the fluid always exists as a single fluid phase and below which two phases may form.

20 **[0040]** The exemplary process described above uses carbon dioxide as the dense fluid, but other dense fluid components may be used for appropriate applications. The dense fluid may comprise one or more components selected from the group consisting of carbon dioxide, nitrogen, methane, oxygen, ozone, argon, helium, ammonia, nitrous oxide, hydrocarbons having 2 to 6 carbon atoms, hydrogen fluoride, hydrogen chloride,
25 sulfur trioxide, sulfur hexafluoride, nitrogen trifluoride, chlorine trifluoride, and fluorocarbons such as, but not limited to, monofluoromethane, difluoromethane,

trifluoromethane, trifluoroethane, tetrafluoroethane, pentafluoroethane, perfluoropropane, pentafluoropropane, hexafluoroethane, hexafluoropropylene (C₃F₆), hexafluorobutadiene (C₄F₆), octafluorocyclobutane (C₄F₈) and methyl fluoride (CH₃F).

[0041] A dense cleaning fluid generally describes a dense fluid to which one or more one or more entrainers have been added. An entrainer is defined as a processing agent which enhances the cleaning ability of the dense fluid to remove contaminants from a contaminated substrate. Further, the entrainer may solubilize and/or disperse the contaminant within the dense cleaning fluid. The dense cleaning fluid typically remains a single phase after an entrainer is added to a dense fluid. Alternatively, the dense cleaning fluid may be an emulsion or suspension containing a second suspended or dispersed phase containing the one or more entrainers. The total concentration of these entrainers in the dense cleaning fluid typically is less than about 50 weight percent and may range from 0.1 to 40 weight percent based upon the weight of the dense cleaning fluid.

[0042] Entrainers generally may include cosolvents, surfactants, chelating agents, chemical modifiers, and other additives. Some examples of representative entrainers are acetylenic alcohols and derivatives thereof, acetylenic diols (non-ionic alkoxylated and/or self-emulsifiable acetylenic diol surfactants) and derivatives thereof, alcohols, quaternary amines and di-amines, amides (including aprotic solvents such as dimethyl formamide and dimethyl acetamide), alkyl alkanolamines (such as dimethanolethylamine), and chelating agents such as beta-diketones, beta-ketoimines, carboxylic acids, mallic acid and tartaric acid based esters and diesters and derivatives thereof, and tertiary amines, diamines and triamines.

[0043] In the present invention, at least one of the entrainers within the dense cleaning fluid is an acetylenic alcohol, an acetylenic diol, or a derivative thereof. The amount of the at least one acetylenic alcohol or acetylenic diol may range from 0.01 to 20 weight

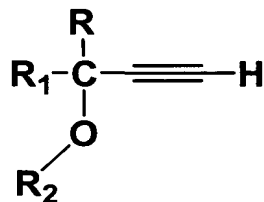
percent, or preferably from 1 to 10 weight percent of the dense cleaning fluid. The acetylenic alcohol and acetylenic diols are commercially available from Air Products and Chemicals, Inc. of Allentown, PA, the assignee of the present invention, under the trade names SURFYNOL® and DYNOL®. Examples of acetylenic alcohols include, for example, 1-hexyne-3-ol ($C_6H_{10}O$), 3,6-dimethyl-1-heptyn-3-ol ($C_9H_{16}O$), 3-methyl-1-pentyn-3-ol ($C_6H_{10}O$), 4-ethyl-1-octyn-3-ol ($C_{10}H_{18}O$), and 3,5-dimethyl-1-hexyn-3-ol ($C_8H_{14}O$ commercially available as SURFYNOL® 61). Examples of acetylenic diols include, for example, 5-decyn-4,7-diol ($C_{10}H_{16}O_2$), 2,5,8,11-tetramethyl-6-dodecyn-5,8-diol ($C_{16}H_{30}O_2$ commercially available as SURFYNOL® 124), 3,6-dimethyl-4-octyn-3,6-diol ($C_{10}H_{18}O_2$ commercially available as SURFYNOL® 82), 5,10-diethyl-7-tetradecyn-6,9-diol ($C_{18}H_{32}O_2$), 2,4,7,9-tetramethyl-5-decyn-4,7-diol ($C_{14}H_{26}O_2$ commercially available as SURFYNOL® 104), ethoxylated 2,4,7,9-tetramethyl-5-decyn-4,7-diol, propoxylated 2,4,7,9-tetramethyl-5-decyn-4,7-diol, butoxylated 2,4,7,9-tetramethyl-5-decyn-4,7-diol, 2,5-dimethyl-3-hexyn-2,5-diol ($C_8H_{14}O_2$ commercially available as DYNOL® 604), ethoxylated 2,5,8,11-tetramethyl-6-dodecyn-5,8-diol, and propoxylated 2,5,8,11-tetramethyl-6-dodecyn-5,8-diol ($C_8H_{14}O$). Acetylenic alcohols or acetylenic diols are preferably soluble within the dense cleaning fluid at a pressure ranging from 1,000 to 7,000 psig, preferably 1,200 to 6,000 psig, and more preferably 1,500 to 4,500 psig. Acetylenic alcohols or acetylenic diols are preferably soluble within the dense cleaning fluid at temperatures ranging from 10 to 70°C, preferably from 20 to 60°C, and most preferably from 35 to 50°C.

[0044] Acetylenic alcohols or diols may be prepared in a number of ways including the methods described, for example, in U. S. Pat. No. 6,313,182 and EP 1115035A1, which are assigned to the assignee of the present invention and incorporated herein by reference in their entirety. One method for preparing these compounds is through the

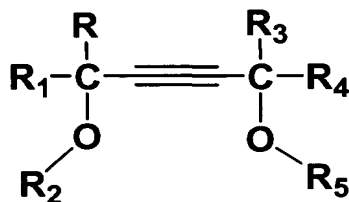
process of ethynylation, or the reaction of acetylene with carbonyl compounds.

Typically, ethynylation uses alkali hydroxide basic catalysts to produce alcohols at lower temperatures and diols (glycols) at higher temperatures.

[0045] The general molecular structures of the acetylenic alcohol and diol surfactants are represented by Formula A and Formula B, respectively.



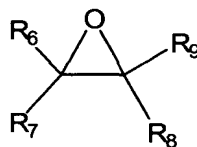
Formula A



Formula B

In the above formulas, R, R₁, R₃, and R₄ are each independently hydrogen atoms, a linear alkyl group comprised of from 1 to 34 carbon atoms, or a branched alkyl group comprised of from 2 to 34 carbon atoms; R₂ and R₅ are each independently a hydrogen atom; a hydroxyl terminated poly-(alkylene oxide) chain derived from 1 to 30 alkylene oxide monomer units, an interactive functional group, and combinations thereof.

[0046] Examples of alkylene oxide monomer units include ethylene oxide (EO), propylene oxide (PO), or a unit represented by Formula C, where R₆, R₇, R₈, and R₉ are independently hydrogen atoms, a linear alkyl group comprised of from 1 to 5 carbon atoms, a branched alkyl group comprised of from 2 to 5 carbon atoms, or a cyclic alkyl group comprised of from 3 to 5 carbon atoms.



Formula C

[0047] In the formulas described herein, the term "alkyl", unless otherwise specified, includes linear alkyl groups, comprised of from 1 to 34 carbon atoms, preferably from 1 to 12 carbon atoms, and more preferably from 1 to 5 carbon atoms; branched alkyl

groups comprised of from 2 to 34 carbon atoms, preferably from 2 to 12 carbon atoms; or cyclic alkyl groups comprised of from 3 to 34 carbon atoms, preferably from 3 to 12 carbon atoms. This term applies also to alkyl moieties contained in other groups such as haloalkyl, alkaryl, or aralkyl. The term "alkyl" further applies to alkyl moieties that are substituted. The term "aryl" as used herein six to twelve member carbon rings having aromatic character. The term "aryl" also applies to aryl moieties that are substituted.

5 [0048] The preferred range of alkoxylation, i.e. the weight percent of ethylene oxide, propylene oxide, or unit represented by Formula C, in an acetylenic alcohol or diol ranges from 0.1 to 85% and depends on the application. For example, in dense cleaning fluid applications using CO₂ as the dense fluid, the ethoxylation ranges from 0.1 to 60%, preferably from 0.1 to 40%, and more preferably from 0.1 to 20%.

10 [0049] In some embodiments of the present invention, substituent R₂ or R₅ in Formulas A or B comprises at least one interactive functional group to provide a derivatized acetylenic alcohol or acetylenic diol. The term "interactive functional group" describes a functional group that interacts with at least one of the contaminants contained within the dense cleaning fluid. The interactive functional group is appended to, or in some instances replaces, the hydrogen atom or the alkylene oxide monomer units at substituent R₂ or R₅.

15 [0050] Derivatized acetylenic alcohols or diols are prepared by reacting reagents having the desired interactive functionality with the acetylenic alcohol or diol, having the Formula A or B, in excess, stoichiometric, or limiting reaction quantities relative to the acetylenic alcohol or acetylenic diol. Stoichiometric or limiting reaction quantities of reagent are preferable to avoid the formation of separate, solid polymeric phases. Reaction conditions such as time, temperature, pressure, atmosphere, etc. may vary

20 based upon the reagent used to provide the interactive functional group. As a result of

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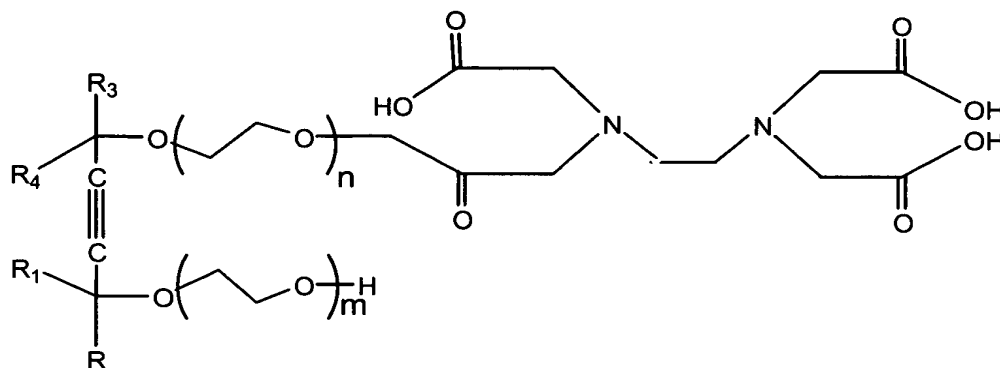
the reaction, the derivatized acetylenic alcohol or diol has at least one interactive functional group bonded thereto and not as a separate solid polymer phase.

[0051] The derivatized acetylenic alcohol or acetylenic diol may obviate the need for adding additional entrainers or processing agents such as, for example, a surfactant or a chelating agent to the dense cleaning fluid. The interactive functional group can be selected to remove a particular contaminant from the substrate. In this regard, dense cleaning fluids can be tailored to selectively remove various contaminants from the substrate such as, for example, inorganics, e.g., metals and metal ions, or organics, e.g., polymeric residues and photoresist.

[0052] Formulas D through I provide non-limiting examples of derivatized acetylenic alcohol or acetylenic diol molecules. Exemplary interactive functional groups include amine and acid functionalities (Formula D); ester functionality (Formula E); ether and alcohol functionalities (Formula F); ester and alcohol functionalities (Formula G); nitrile functionalities (Formula H); and carbonate functionalities (Formula I). Still other reagents to provide at least one interactive functional group within the derivatized acetylenic alcohol or diol molecules include alkyl polyglycosides or other sugar derivatives. In formulas D through I, substituent R_2 or R_5 includes the functional group provided by the reagent and the value of $m+n$ in each formula defines the amount of alkylene oxide monomer units in the initial alcohol or diol molecule to which the interactive functional group is appended thereto. In some embodiments, such as when the value of $m+n$ in the initial alcohol or diol equals zero, the derivatized alcohol or diol contains no alkylene oxide monomer units at R_2 and/or R_5 .

[0053] The derivatized acetylenic alcohol or diol may have one or more acid and amine groups as the interactive functional group. Formula D provides an example of a derivatized diol wherein substituent R_5 is an acid and amine functional group and the value of $m+n$ is a number ranging from 0 to 30. In these embodiments, the acetylenic

diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, ethylenediamine tetraacetate anhydride, to provide a derivatized acetylenic alcohol or diol containing varying amounts of an acid and amine functionality.



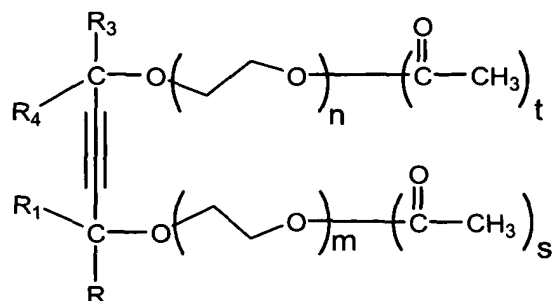
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Formula D

[0054] In an alternative embodiment, the amount of acetylenic alcohol and/or acetylenic diol may be present in relatively higher concentrations than the reagent used to provide the interactive functional group during the reaction. In these embodiments, only a portion of the acetylenic alcohol or diol is derivatized. For example, an excess of the acetylenic alcohol or acetylenic diol may be reacted with the ethylenediamine tetraacetate anhydride reagent to provide a molecule comprising 2 acetylenic alcohol or acetylenic diol molecules associated with one ethylenediamine tetraacetate anhydride. By contrast, the compound in Formula D comprises 1 ethylenediamine tetraacetate anhydride molecule associated with one acetylenic alcohol or diol molecule.

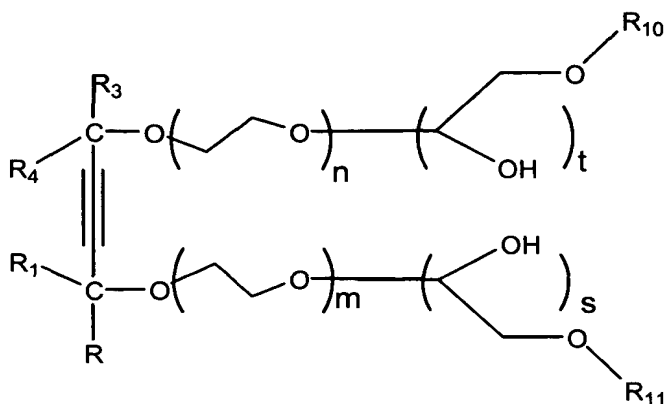
15 **[0055]** The derivatized acetylenic alcohol or diol may have one or more ester functionalities as the interactive functional group. In these embodiments, the acetylenic diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, acetyl chloride to provide a derivatized acetylenic alcohol or diol containing varying amounts of an ester functionality. Formula E provides an example of a derivatized diol

wherein substituent R_5 is an ester functional group, the value of $m+n$ is a number ranging from 0 to 30, and the value of $s+t$ is a number ranging from 1 to 2.



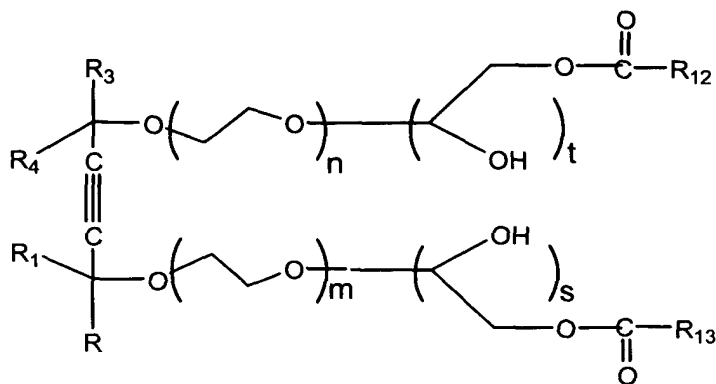
Formula E

- 5 **[0056]** The derivatized acetylenic alcohol or diol may have one or more ether and alcohol functionalities as the interactive functional group. In these embodiments, the acetylenic diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, glycidyl methylether, glycidyl isopropylether, glycidyl butylether, glycidyl tetrafluoroethylether or other glycidyl alkylethers or glycidyl fluoroalkylethers, to provide a
- 10 derivatized acetylenic alcohol or diol containing varying amounts of combined ether and alcohol functionalities. Formula F provides an example of a derivatized diol wherein substituent R_5 is an ether and alcohol functional group, the value of $m+n$ is a number ranging from 0 to 30, and the value of $s+t$ is a number ranging from 1 to 2, and R_{10} and R_{11} are each independently a linear alkyl or fluoroalkyl group comprised of from 1 to 34
- 15 carbon atoms; a branched alkyl or fluoroalkyl group comprised of from 2 to 34 carbon atoms; or a cyclic alkyl or fluoroalkyl group comprised of from 3 to 34 carbon atoms.



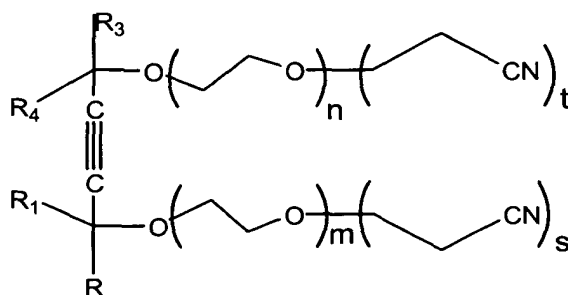
Formula F

[0057] The derivatized acetylenic alcohol or diol may have one or more ester and alcohol functionalities as the interactive functional group. In these embodiments, the acetylenic diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, glycidyl acetate, glycidyl butyrate, glycidyl benzoate, glycidyl methacrylate or other glycidyl esters to provide a derivatized acetylenic alcohol or diol containing varying amounts of a combined ester and alcohol functionalities. The glycidyl reagent may also be a glycidyl nitrobenzoate, a glycidyl carboxamide, a glycidyl tosylate or a glycidoxypropyldimethylethoxysilane to provide other desired chelating or solubilizing functionalities. Formula G provides an example of a derivatized diol wherein substituent R_5 is an ester and alcohol functional group, the value of $m+n$ is a number ranging from 0 to 30, the value of $s+t$ is a number ranging from 1 to 2, and R_{12} and R_{13} are each independently a linear alkyl or fluoroalkyl group comprised of from 1 to 34 carbon atoms; a branched alkyl or fluoroalkyl group comprised of from 2 to 34 carbon atoms; or a cyclic alkyl or fluoroalkyl group comprised of from 3 to 34 carbon atoms.



Formula G

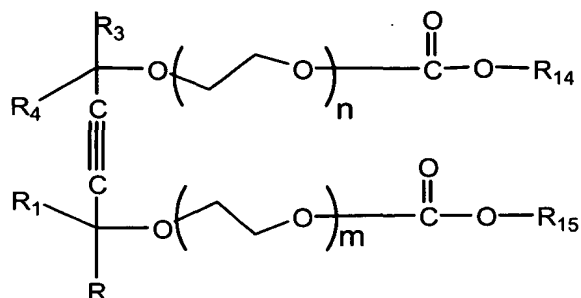
[0058] The derivatized acetylenic alcohol or diol may have one or more nitrile functionalities as the interactive functional group. In these embodiments, the acetylenic diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, acrylonitrile or other nitrile monomer to provide a nitrile end-capped derivatized acetylenic alcohol or diol containing varying amounts of nitrile functionality. Formula H provides an example of a derivatized diol wherein substituent R₅ is a nitrile functional group, the value of m+n is a number ranging from 0 to 30, and the value of s+t is a number ranging from 1 to 2.



Formula H

[0059] The derivatized acetylenic alcohol or diol may have one or more carbonate functionalities as the interactive functional group. In these embodiments, the acetylenic diol or acetylenic alcohol may be reacted with at least one reagent such as, for example, an alkylene carbonate to provide an alkyl carbonate end-capped acetylenic alcohol or

diol containing varying amounts of carbonate functionality. Formula I provides an example of a derivatized diol wherein substituent R_5 is a nitrile functional group, R_{14} and R_{15} are each independently a linear, branched, or cyclic alkyl group comprised of from 1 to 34 carbon atoms, the value of $m+n$ is a number ranging from 0 to 30, and the value of $s+t$ is a number ranging from 1 to 2.



Formula I

[0060] As mentioned previously, further entrainers that may be added to the dense cleaning fluid include, but are not limited to, cosolvents, surfactants, chelating agents, chemical modifiers, or other additives. The total concentration of these additional entrainers in the dense cleaning fluid typically is less than about 50 weight percent, and may range from 0.1 to 40 weight percent.

[0061] In embodiments wherein a cosolvent is added to the dense cleaning fluid, the cosolvent is preferably at least one cosolvent selected from the group consisting of esters (ethyl acetate, ethyl lactate), ethers (diethyl ether, dipropyl ether), alcohols (methanol, isopropanol), nitriles (acetonitrile, propionitrile, benzonitrile), hydrated nitriles (ethylene cyanohydrin), glycols (ethylene glycol, propylene glycol), monoester glycols (ethylene glycol monoacetate), ketones (acetone, acetophenone) and fluorinated ketones (trifluoroacetophenone), tertiary amines including pyridines (triethyl amine, tributyl amine, 2,4, dimethyl pyridine), alkanolamines (dimethylethanolamine, diethylethanolamine), amides (dimethylformamide, dimethylacetamide), carbonates

(ethylene carbonate, propylene carbonate), carboxylic acids (acetic acid, tartaric acid, malic acid), alkane diols (butane diol, propane diol), alkanes (n-hexane, n-butane), peroxides (hydrogen peroxide, t-butyl hydroperoxide, 2-hydroperoxy hexafluoropropan-2-ol), water (deionized, ultrahigh purity), ureas, haloalkanes (perfluorobutane,

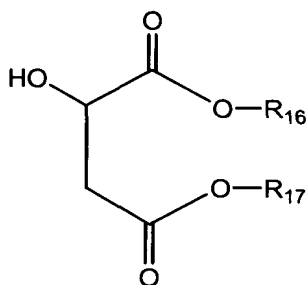
5 hexafluoropentane), haloalkenes, and combinations thereof. The amount of cosolvent added to the dense fluid may range from 1 to 40 weight percent, preferably from 1 to 20 weight percent, and more preferably from 1 to 10 weight percent. In preferred embodiments, the cosolvent is a nitrile compound, such as benzonitrile, propionitrile, or acetonitrile, which is present in the dense cleaning in an amount ranging from 1 to 20
10 weight percent, preferably from 1 to 10 weight percent.

[0062] Chelating agents may also be added to the dense cleaning fluid in an amount ranging from 0.01 to 20 weight percent, or more preferably from 1 to 5 weight percent. Examples of suitable chelating agents include, but are not limited to a beta-diketones such as acetylacetone, acetonyl acetone, trifluoroacetylacetone, thenoyltrifluoroacetone,
15 or hexafluoroacetylacetone, a carboxylic acid such as citric acid, malic acid, oxalic acid, or tartaric acid, a malic acid ester and/or diester, a tartaric acid ester and/or diester, an oxime such as 8-hydroxyquinoline, a tertiary amine such as 2-acetyl pyridine, a tertiary diamine, a tertiary triamine, a nitrile such as ethylene cyanohydrin, a beta-ketoimine, ethylenediamine tetraacetic acid and its derivatives, catechol, choline-containing
20 compounds, trifluoroacetic anhydride, an oxime such as dimethyl glyoxime, dithiocarbamates such as bis(trifluoromethyl)dithiocarbamate, terpyridine, ethylene cyanohydrin, N-(2-hydroxyethyl)iminodiacetic acid, and combinations thereof.

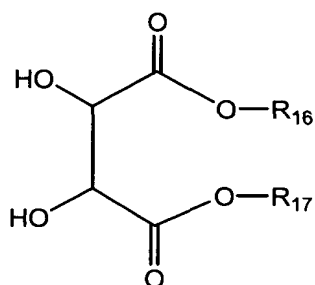
[0063] In one embodiment of the present invention, one or more chelating agents within the dense cleaning fluid may be a malic acid diester, a tartaric acid diester, or
25 derivatives thereof. In these embodiments, the amount of the malic acid diester entrainer or the tartaric acid diester entrainer within the dense cleaning fluid may range

from 0.01 to 20 weight percent, or preferably from 1 to 10 weight percent. The malic acid diester and tartaric acid diester are very soluble in dense CO₂ fluids and are may be effective as entrainers at removing photoresist and photoresist residue. These molecules and their methods of preparation have been described, for example, in US 6,423,376B1, US 6,369,146B1, and US 6,544,591B2, which are assigned to the assignee of the present invention and incorporated herein by reference in their entirety.

[0064] Exemplary malic acid diesters and tartaric acid diesters are represented by the following Formula J and K:



Structure J



Structure K

where R₁₆ and R₁₇ are independently a linear or haloalkyl group comprised of from 1 to 20 carbon atoms; a branched alkyl or haloalkyl group comprised of from 2 to 20 carbon atoms; or a cyclic alkyl or haloalkyl group comprised of from 3 to 20 carbon atoms.

Substituents R₁₆ and R₁₇ may be the same or different; however, symmetrical malates or tartrates, i.e., where R₁₆ and R₁₇ are identical, are preferred due to ease of synthesis.

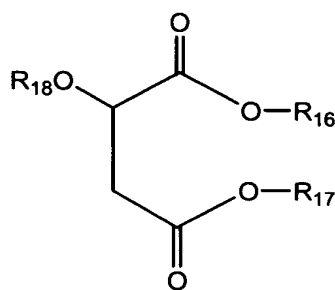
Stereo isomers of the malic acid diesters or tartaric acid diesters are also suitable for the present invention. Suitable alkyl groups for the diesters, also known as dialkylmalates and dialkyltartrates, include, for example, methyl, ethyl, n-propyl, isopropyl, n-butyl, isobutyl, sec-butyl, n-pentyl, 3-methyl-2-butyl, cyclopentyl, cyclohexyl, 2-ethylhexyl, and dodecyl groups. The alkyl groups may further include one or more halogen atoms such as haloalkyl groups, preferably fluoroalkyl groups. Malic acid diesters and tartaric acid

diesters are soluble within the dense cleaning fluid at pressures ranging from 1,000 to 7,000 psig, preferably 1,200 to 6,000 psig, and more preferably 21,500 to 4,500 psig. They are soluble at temperatures ranging from 10 to 70°C, preferably from 20 to 60°C, and most preferably from 35 to 50°C.

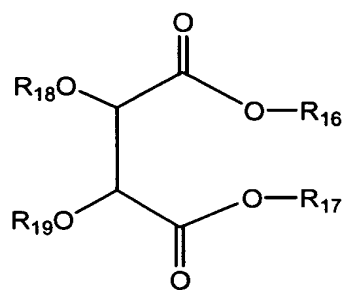
5 **[0065]** In other embodiments of the present invention, the malic acid diester or tartaric acid diester may be reacted with a reagent containing at least one interactive functional group to provide a derivatized malic acid diester or a derivatized tartaric acid diester. In these embodiments, reagents having the desired functionality are reacted with the diester in excess, stoichiometric, or limiting reaction quantities relative to the diester.

10 Stoichiometric or limiting reaction quantities of reagent are preferable to avoid the formation of separate, solid polymeric phases. Reaction conditions such as time, temperature, pressure, atmosphere, etc., may vary based upon the reagent used to provide the functional group. As a result of the reaction, the diester has an interactive functional group bonded thereto and not as a separate solid polymer phase. Like the
15 derivatized acetylenic alcohol or derivatized acetylenic diol, the derivatized diesters may obviate the need for adding separate entrainers such as a surfactant and a chelating agent to the dense cleaning fluid. Further, one or more interactive functional groups on the diester may be selected to remove a particular contaminant from the substrate.

20 **[0066]** Exemplary derivatized malic acid diesters and tartaric acid diesters are represented by the following Formula L and M:



Formula L



Formula M

In the preceding formula, substituent R_{18} and R_{19} are one or more interactive functional groups provided by the reagent. Exemplary interactive functional groups R_{18} and R_{19}

- 5 include, but are not limited to, acids, amines, acetates, amino acetates, glycidyl ethers or esters, carbonates, tertiary amines, beta-diketones, beta-ketoimines, alkenes, and nitriles. In one embodiment, the malic acid diester or tartaric acid diester may be reacted with ethylenediamine tetraacetate anhydride to provide a derivatized malic acid diester or derivatized tartaric acid diester containing varying amounts of an amine and acid
- 10 functionality. In other embodiments, the malic acid diester or tartaric acid diester may be reacted with acetyl chloride to provide a derivatized malic acid diester or derivatized tartaric acid diester containing varying amounts of an ester functionality; reacted with glycidyl methylether, glycidyl isopropylether, glycidyl butylether, glycidyl tetrafluoroethylether or other glycidyl alkylethers or glycidyl fluoroalkylethers to provide a
- 15 derivatized malic acid diester or tartaric acid diester containing varying amounts of combined ether and alcohol functionalities; reacted with glycidyl acetate, glycidyl butyrate, glycidyl benzoate, glycidyl methacrylate, or other glycidyl esters to provide a derivatized malic acid diester or tartaric acid diester containing varying amounts of a combined ester and alcohol functionalities. The glycidyl reagent may also be a glycidyl
- 20 nitrobenzoate, a glycidyl carboxamide, a glycidyl tosylate, or glycidoxypropyldimethylethoxysilane to provide other desired chelating or solubility functionalities. In other embodiments, the malic acid diester or tartaric acid diester may

be reacted with acrylonitrile or other nitrile monomers to provide a nitrile end-capped derivatized malic acid diester or derivatized tartaric acid diester containing varying amounts of nitrile functionality. In yet another embodiment, the malic acid diester or tartaric acid diester may be reacted with an alkylene carbonate to provide an alkyl
5 carbonate end-capped malic acid diester or tartaric acid diester containing varying amounts of carbonate functionality.

[0067] In formulations wherein a cosolvent and a chelating agent is added to the dense cleaning fluid, the composition of the dense cleaning fluid comprises from 50 to 99 weight percent of dense fluid, from 1 to 20 weight present of a cosolvent, from 1 to 10
10 weight percent of at least one acetylenic diol or acetylenic alcohol, and from 0.1 to 10 weight percent of a chelating agent. In certain preferred embodiments, the dense cleaning fluid comprises from 65 to 99 weight percent of a dense fluid such as liquid/supercritical CO₂, from 1 to 20 weight percent of a co-solvent such as a nitrile compound, from 1 to 10 weight percent at least one acetylenic alcohol or acetylenic diol,
15 and from 0.1 to 5 weight percent of a chelating agent. The specific composition of the dense cleaning fluid depends on the application. Exemplary formulations for various substrate treatment applications are provided in Table I.

Table I: Exemplary Formulations for Various Substrate Treatment Applications

Application	Dense Fluid	Acetyl nic Alc h I or Acetylenic Diol	Cosolvent	Chelating Ag nt
Post-etch cleaning (metals)	Liquid or Supercritical CO ₂ Supercritical C ₂ F ₆	Surfynol®61, Surfynol®420, Dynol®604 Hydrogenated Surfynol®104	Tertiary ammonium hydroxides(TMAH, TBAH), Alkanolamines, Nitriles	Dibutyl mallate Dipentyl tartrate Diisoamyl tartrate
Post-etch cleaning (polymers)	Liquid or Supercritical CO ₂ Supercritical C ₂ F ₆	Surfynol®61, Surfynol®420, Dynol®604, Hydrogenated Surfynol®104	TMAH, TBAH, Alkanolamines, Nitriles, Tertiary amines	
Post-CMP cleaning	Liquid or Supercritical CO ₂	Surfynol®61, Surfynol®2502 Surfynol®420 Hydrogenated Surfynol®104	TMAH, TBAH, Alkanolamines, Tertiary amines	Dibutyl mallate, Dipentyl tartrate, Diisoamyl tartrate, Carboxylic acids
Photoresist removal/stripping	Liquid or Supercritical CO ₂	Surfynol®61, Surfynol®420, Dynol®604, Hydrogenated Surfynol®104	Nitriles, Tertiary amines, Acetophenone, Alkanolamines	
Ash residue removal	Liquid or Supercritical CO ₂	Surfynol®61, Surfynol®420, Dynol®604, Hydrogenated Surfynol®104	Alkanolamines, Tertiary amines, Nitriles	Dibutyl mallate, Dipentyl tartrate, Diisoamyl tartrate, Carboxylic acids

[0068] The substrate containing the contaminants may be contacted with the dense cleaning fluid using a variety of different apparatus and operating conditions. The actual conditions of the contacting step (i.e., temperature, pressure, contact time, and the like) may vary over wide ranges and are generally dependent on a variety of factors such as, but not limited to, the nature and amount of residue on the surface of the substrate, the solubility of the one or more entrainers in the dense fluid, the phobicity or philicity of the contaminant(s) withing the dense cleaning fluid, etc. The duration of the contacting step, or time of contact of the dense cleaning fluid with the substrate surface, can vary from a fraction of a second to hundreds of seconds. Preferably, the duration can range from 0.1 to 600 seconds, more preferably from 1 to 300 seconds, and most preferably from 15 to 240 seconds.

[0069] The dense cleaning fluid can be contacted with the substrate using either a dynamic method, a static method, or combinations thereof. In the dynamic method, a dense cleaning fluid is applied to the substrate by flowing or spraying the fluid, such as for example, by adjusting inlet flow and pressure, to maintain the necessary contact time.

5 Alternatively, the contact step may be conducted using a static method such as for example, immersing the substrate within a chamber containing the dense cleaning fluid or applying the dense cleaning fluid to the substrate and allowing it to contact the dense cleaning fluid for a certain period of time.

[0070] In some embodiments, the dense fluid can be applied to the surface of the
10 substrate after the introduction of the entrainer (acetylenic alcohol and/or acetylenic diol) and optional additives, by first treating the substrate with the entrainer and optional additives and then placing the substrate in contact with the dense fluid to provide the dense cleaning fluid. Alternatively, the dense fluid and the acetylenic alcohol and/or acetylenic diol and optional additives may be introduced into the vessel sequentially,
15 such as, for example, by first introducing the dense fluid and subsequently introducing the entrainer (acetylenic alcohol and/or acetylenic diol) and optional additives. In this case, the dense cleaning fluid may be formed in multiple steps during the processing of the substrate. In still further embodiments of the present invention, the entrainer can be deposited upon or comprise the material of a high surface area device such as a
20 cartridge or filter (which may or may not include other additives). A stream of dense fluid then passes through the cartridge or filter thereby forming the dense cleaning fluid. In still another embodiment of the present invention, the dense cleaning fluid is prepared during the contacting step. In this connection, at least one entrainer is introduced via a dropper or other means to the surface of the substrate. The dense fluid medium is then
25 introduced to the surface of the substrate which mixes with the at least one entrainer on the surface of the substrate thereby forming the dense cleaning fluid. Other alternatives

include immersing the substrate in a pressurized, enclosed chamber and then introducing the appropriate quantity of entrainer.

[0071] Typically, the contacting step may be performed by placing a substrate having contaminants within a high pressure chamber and heating the chamber to the desired temperature. The substrate may be placed vertically, at an incline, or preferably in a horizontal plane. The dense cleaning fluid can be prepared prior to its contact with the substrate surface. For example, a certain quantity of one or more entrainers (acetylenic alcohols and/or acetylenic diols) can be injected into a continuous stream of the dense fluid medium that optionally includes other entrainers and/or additives thereby forming the dense cleaning fluid. The dense cleaning fluid can also be introduced into the heated chamber before or after the chamber has been pressurized to the desired operating pressure.

[0072] In one particular embodiment, the desired pressure can be obtained by introducing dense fluid into an enclosed chamber. In this embodiment, additional entrainers (e.g., co-solvents, chelating agents, and the like) may be added at an appropriate time prior to and/or during the contacting step. The entrainer, or a mixture thereof, forms the dense cleaning fluid after the entrainer and dense fluid have been combined. The dense cleaning fluid then contacts the substrate and the contaminant associates with the entrainer and/or mixture thereof, and becomes entrained in the fluid. Depending on the conditions employed in the separation process, varying portions of the contaminant may be removed from the substrate, ranging from relatively small amounts to nearly all of the contaminant.

[0073] During the contacting step, the chamber temperature can preferably range from 10 to 100°C, more preferably from 20 to 70°C, and most preferably from 25 to 60°C. The operating pressure can preferably range from 1000 psig to 8000 psig (69 to 552 bar), more preferably from 2000 psig to 6000 psig (138 to 414 bar), and most preferably from

2500 to 4500 psig (172 to 310 bar). Optional agitation methods such as ultrasonic energy, mechanical agitation, gas or liquid jet agitation, pressure pulsing, or any other suitable mixing technique may be used to enhance cleaning efficiency and contaminant removal.

5 **[0074]** An embodiment of the invention can be illustrated by the delivery and use of a dense processing fluid for use in the cleaning or processing of an article such as a microelectronic component. An exemplary process for this embodiment is provided in Figure 4. Figure 4 illustrates a system in which dense cleaning fluid is contacted with the entrainer (at least one acetylenic alcohol or acetylenic diol), and optionally other
10 entrainers and/or additives, prior to being introduced to cleaning chamber 27. A dense fluid stream 39 from a bulk fluid source 19 is supplied to an intermediate storage device 21 such as a tank or a Y container. The dense fluid may be stored as a dense gas, a liquid or a supercritical fluid, or preferably as a liquid at ambient temperature. Pumping device 23 helps increase the pressure of the dense fluid stream 41 from the intermediate
15 storage device 21 prior to its entry into heating device 26.. Pumping device 23 can be a pump, a compressor, or any other device capable of increasing pressure at a set flow rate. Preferably, pumping device 23 is a diaphragm pump. High pressure fluid stream 43 is brought to processing temperature by heating device 26 prior to being contacted with the acetylenic alcohol and/or acetylenic diol entrainer and any optional entrainers
20 and/or additives.

[0075] The acetylenic alcohol and/or acetylenic diol entrainer stream 57 is supplied from an entrainer intermediate storage device 31 and is pumped to the desired operating pressure by the entrainer pumping device 33. The optional additive stream 65 is supplied from an additive intermediate storage device 35 and is pumped to the desired
25 operating pressure by the additive pumping device 37. The contents of the high pressure entrainer and additive streams, 61 and 63 respectively, are then intimately

contacted with the heated dense fluid stream 47 to create a dense fluid cleaning stream 49. Alternatively, pressurized streams 61 and 63 can be contacted with the dense fluid stream 43 prior to heating with heater 26. The advantage of this alternative embodiment is that all streams are heated evenly prior to introduction into the cleaning chamber 27.

5 In a still further embodiment, the additives can be premixed with the at least one acetylenic alcohol and/or diol entrainer prior to pressurization and delivery, thereby obviating the need for the additive intermediate storage device and the additive pumping device.

[0076] Cleaning chamber 27 is subsequently purged (rinsed) with purified dense fluid
10 to ensure that the contaminants are separated from the substrate and to prevent redeposition of the contaminants. The rinse also ensures removal of any entrainer and additive from the process chamber. Subsequently, the contaminant is separated from the dense fluid. Any known technique may be employed for this step. In one embodiment, temperature and pressure profiling of the fluid is employed to vary the
15 solubility of the contaminant in the dense fluid such that it separates out of the fluid. In addition, the same technique may be used to separate the entrainer from the dense fluid. Additionally, a co-solvent, co-surfactant, or any other additive material can be separated. In the embodiment depicted in Figure 4, separator 29 is used to separate the dense fluid stream 53 from the entrainer and optional additive stream 55. Any of the materials may
20 be recycled for subsequent use in accordance with known methods. For example, the temperature and pressure of the vessel may be varied to facilitate removal of residual entrainer or additives from the substrate being cleaned.

[0077] Dense cleaning fluids prepared and managed by the methods of the present invention may be used in other processing steps in the manufacture of electronic
25 components in which material is removed from a part (etching, drying, or planarization),

in which material is deposited on a part (thin film deposition), or in which material on a part is chemically modified (photoresist development).

[0078] In applying the present invention, semiconductor substrates may be cleaned or processed individually in order to provide direct process integration with other, single
5 substrate processing modules. Alternatively, multiple substrates, or batches, may be cleaned or processed simultaneously in a container or "boat" placed within the cleaning or processing chamber, thereby providing high throughput and reduced cost of operation.

[0079] The following Examples illustrate embodiments of the present invention but do
10 not limit the embodiments to any of the specific details described therein.

EXAMPLES

Examples 1 through 12a: Solubility of Various Additives within a Dense Fluid

[0080] In the following examples, mixtures of entrainers such as acetylenic alcohols,
15 acetylenic diols, co-solvents, and chelating agents with liquid/supercritical CO₂ as the dense fluid were prepared by adding the one or more entrainers to a stainless steel variable volume high-pressure view cell equipped with suitable pressure relief devices, high-pressure inlet and outlet valves, a magnetic stirrer for agitating the mixture, pressure transducer, an internal thermocouple, and a sapphire window at one end. The
20 cell is mounted horizontally and equipped with a heating/cooling jacket through which a cooling/heating fluid is circulated. A circulating bath was used to supply and pump the cooling/heating fluid to ensure isothermal (constant temperature) operation. The pressure in the cell was adjusted by changing the position of a piston. The moving piston was viewed through the sapphire window using a suitable optic device and the
25 image was transmitted to a video screen. A description of the vessel is given in the

Journal of Physical Chemistry 94 (1990), pp 6021 which is incorporated herein by reference in its entirety.

[0081] A high-pressure syringe pump (High Pressure Products HIP pump) was filled with liquid CO₂ and used to add CO₂ to the pressure vessel. A weighed amount of surfactant or co-solvent, ranging from 1 to 30 weight percent, was charged inside the chamber of the cell in front of the piston. The identity and amount of each reagent within the mixture is provided in Table II. The cell window was attached and approximately 10 to 15 cc of CO₂ was added to the chamber of the cell while maintaining the cell temperature at a relatively constant value (24-26°C) to provide a mixture. After the chamber of the cell had been charged with the appropriate amount of CO₂, the cooling bath temperature was adjusted to maintain the desired cell temperature (35-60°C). After the cell had attained thermal equilibrium, the pressure within the cell chamber was gradually increased in increments of 5 bar. The cell was monitored through the sapphire window until the cloud point of the mixture, or the point where the image within the sapphire window changes from being translucent to clear/transparent and vice-versa, was observed. The pressure and temperature at which the cloud point occurred was noted as being indicative of solubility of the mixture and is provided in Table II. The onset of solubility/insolubility was verified by varying the pressure, i.e., cycling the pressure above and below its cloud point value.

[0082] The results in Table II illustrate that the preferred entrainers of this invention, i.e., acetylenic alcohols, acetylenic diols, nitriles, and chelating agents such as dibutyl mallate, are remarkably soluble in liquid and supercritical CO₂. The supercritical CO₂ results (CO₂ is in the supercritical phase at temperatures above 31°C and pressures above 73 bar) indicate that several acetylenic alcohols and acetylenic diols including Surfynol®61, Surfynol®420, Hydrogenated Surfynol®104, and Dynol®604 can be

dissolved in relatively larger quantities, e.g., 5-10 wt %, in supercritical CO₂ at moderate pressure and temperature conditions, e.g., pressures below 200 bar or approximately 3000 psig. The solubility of acetylenic alcohols and acetylenic diols in supercritical CO₂ is as good as, or better than, well known but more expensive CO₂-soluble species like

5 fluoracrylates and polydimethylsiloxane at the same temperature and pressure conditions. For example, at a fixed composition (5 wt %) and temperature (35°C), a silicone-based entrainer such as that depicted in example 12a is soluble only at pressures above 172.5 bar, whereas in examples 1c and 2c Surfynol®61 and Surfynol®420 are soluble at pressures above 137.5 bar and 150.0 bar, respectively.

10 Further, the high solubility of Surfynol®61 and Hydrogenated Surfynol®104 at low pressures makes them particularly useful as a part of any cost-effective dense fluid CO₂-based cleaning or substrate treatment formulation.

[0083] The results for liquid CO₂ at ambient temperature (approximately 25°C) indicate that all the nitriles (benzonitrile, propionitrile, acetonitrile) are miscible in liquid CO₂ or

15 dissolve upon agitation. The results also indicate that nitriles (benzonitrile, acetonitrile and propionitrile) are soluble at a concentration of up to 20 wt % in supercritical CO₂ at pressures below 140 bar, or approximately 2050 psig. Thus, they can be efficiently used individually, or as co-solvents in conjunction with acetylenic alcohols and acetylenic diols, to remove contaminants at pressures below 3000 psig and temperatures up to

20 60°C, because they may help increase the solubility and miscibility of the acetylenic alcohols and diols in dense fluid CO₂

Table II: Liquid and Supercritical Solubility of Various Additives

Example Number	Entrainers	Wt % of Entrainer	Temp. (°C)	Average Pressure (bar)	Comments
Ex. 1a	Surfynol®61	10	35	137.5	Soluble at > 10 wt %
Ex. 1b	Surfynol®61	10	50	106.0	Soluble at > 10 wt %
Ex. 1c	Surfynol®61	5	35	137.5	
Ex. 2a	Surfynol®420	10	35	139.5	
Ex. 2b	Surfynol®420	10	50	187.5	
Ex. 2c	Surfynol®420	5	35	150.0	
Ex. 2d	Surfynol®420	5	50	190.0	
Ex. 3a	Diethylethanolamine	5.35	37-38	147.5	
Ex. 3b	Diethylethanolamine	6.19	41-42	160.0	
Ex. 4a	Hydrogenated Surfynol®104	10	35	117.5	
Ex. 4b	Hydrogenated Surfynol®104	10	50	147.5	
Ex. 4c	Hydrogenated Surfynol®104	5	35	98.5	
Ex. 4d	Hydrogenated Surfynol®104	5	50	135.5	
Ex. 5a	Dibutyl mallate	10	35	87.5	Appears to coat window
Ex. 5b	Dibutyl mallate	10	50	121.5	Appears to coat window
Ex. 6a	Benzonitrile	19	25.4	69.5	Soluble in liquid CO ₂
Ex. 6b	Benzonitrile	19	35.3	80.0	
Ex. 7a	Acetonitrile	20	23.7	70.6	Soluble in liquid CO ₂
Ex. 7b	Acetonitrile	20	34.0	131.2	
Ex. 8a	Acetophenone	10	34.9	82.3	
Ex. 8b	Acetophenone	28	24.6	68.3	Soluble in liquid CO ₂
Ex. 9a	Tri-n-butyl-amine	10	24.3	70.4	Soluble in liquid CO ₂
Ex. 9b	Tri-n-butyl-amine	10	35.2	78.2	
Ex. 10a	Propionitrile	19	23.9	71.2	Soluble in liquid CO ₂
Ex. 10b	Propionitrile	19	34.7	137.5	
Ex. 11a	Methyl-ethyl-ketone	20	24.7	68.2	Soluble in liquid CO ₂
Ex. 11b	Methyl-ethyl-ketone	20	34.9	128.5	
Ex. 12	Dynol™604	5	24.7	157.5	
Ex 12a	Silicone-based surfactant	5	35.0	172.5	

Examples 13 through 18: Solubility of Acetylenic Alcohol and Diol-Based Mixtures in Liquid and Supercritical CO₂

[0084] The process of Examples 1 through 12 is repeated using different mixtures of entrainers to determine the miscibility and solubility in liquid and supercritical CO₂. The solubility results are shown in Table III. The results indicate that all mixtures except propionitrile-Dynol®604 (50/50) are soluble in liquid CO₂. The results also indicate that the mixtures are soluble in supercritical CO₂ (SC-CO₂) at pressures less than 3400 psig (~ 235 bar) at all temperatures. In many cases, the pressure required to dissolve an acetylenic alcohol or diol-based mixture in liquid or supercritical CO₂ for a given weight percent and temperature is lower than the pressure required to render a fluorinated or silicone-based entrainer soluble at the same temperature and weight percent.

Table III: Liquid and Supercritical CO₂ Solubility of Acetylenic Alcohol and Diol-Based Mixtures

Example Number	Entrainer Mixture (wt/wt)	Mixture wt % in CO ₂	Temp. (°C)	Average Pres. (bar)	Comments
13a	Benzonitrile/Surfynol®61 (50/50)	10	24.7	69.5	Miscible in liquid CO ₂
13b	Benzonitrile/Surfynol®61 (50/50)	10	41.3	95.0	
13c	Benzonitrile/Surfynol®61 (50/50)	10	60.5	138.0	
14a	Benzonitrile/Surfynol®420 (50/50)	9	24.4	76.3	Miscible in liquid CO ₂
14b	Benzonitrile/Surfynol®420 (50/50)	9	41.0	122.5	
14c	Benzonitrile/Surfynol®420 (50/50)	9	60.0	163.2	
15a	Benzonitrile/Dynol®604 (50/50)	9	24.1	71.5	Miscible in liquid CO ₂
15b	Benzonitrile/Dynol®604 (50/50)	9	40.7	140.3	
15c	Benzonitrile/Dynol®604 (50/50)	9	60.5	218.4	
15d	Benzonitrile/Dynol®604 (50/50)	5	24.3	68.9	Miscible in liquid CO ₂
15e	Benzonitrile/Dynol®604 (50/50)	5	41.0	133.6	
15f	Benzonitrile/Dynol®604 (50/50)	5	60.0	205.5	
16a	Propionitrile/Surfynol®61 (50/50)	10	24.3	70.0	Miscible in liquid CO ₂
16b	Propionitrile/Surfynol®61 (50/50)	10	41.5	91.0	Excessive reflux in cell
16c	Propionitrile/Surfynol®61 (50/50)	10	61.2	119.5	Excessive reflux in cell
16d	Propionitrile/Surfynol®61 (50/50)	5	24.0	68.7	Miscible in liquid CO ₂
16e	Propionitrile/Surfynol®61 (50/50)	5	41.2	100.7	Cell vol. at max limit
16f	Propionitrile/Surfynol®61 (50/50)	5	60.8	159.6	Cell vol. at max limit
17a	Propionitrile/Surfynol®420 (50/50)	10	23.7	68.6	Miscible in liquid CO ₂
17b	Propionitrile/Surfynol®420 (50/50)	10	41.5	106.0	
17c	Propionitrile/Surfynol®420 (50/50)	10	61.0	140.0	
17d	Propionitrile/Surfynol®420 (50/50)	5	24.9	69.7	Miscible in liquid CO ₂
17e	Propionitrile/Surfynol®420 (50/50)	5	40.9	97.2	Cell vol. at max

					limit
17f	Propionitrile/Surfynol®420 (50/50)	5	60.5	155.2	Cell vol. at max limit
18a	Propionitrile/Dynol®604 (50/50)	11	41.0	149.5	Insoluble in liquid CO ₂
18b	Propionitrile/Dynol®604 (50/50)	11	60.5	228.2	Got cloudy slowly
18c	Propionitrile/Dynol®604 (50/50)	6	41.4	151.7	Insoluble in liquid CO ₂
18d	Propionitrile/Dynol®604 (50/50)	6	60.3	232.3	Got cloudy slowly

Examples 19 through 35: Photoresist Dissolution and Removal Results

[0085] For the following examples, mixtures of entrainers such as acetylenic alcohols, acetylenic diols, co-solvents, and chelating agents with either ultra-pure-water (UPW) or hexanes (primarily n-hexane) as the solvent were prepared. Hexanes are considered good “surrogate” solvents for supercritical CO₂ because the solubility parameters of n-hexane and supercritical CO₂ at 3000 psia and 50°C are very similar. Experimental results also indicate that solvating power of the two solvents (supercritical CO₂ and n-hexane) differs by at the most approximately 20%. The identity and amount of each entrainer in the mixture is provided in Table IV. Centrifuge tubes were filled with 20 ml of each mixture and placed in a circulating bath at 35°C for at least 10 minutes. Restored 4-inch diameter wafers supplied by Wafer Net were blown off with a high-pressure nitrogen gun to remove surface particulates and then measured using a Filmetrics F20 Thin Film Measurement System in three regions of the wafer. The measurements were then recorded and averaged.

[0086] Each wafer was coated with photoresist as follows. The wafer was placed in the center of a Headway Model 1-EC10D-R790 Precision Spin-coater vacuum chuck within an enclosed hood. A 2ml amount of Sumitomo 193 nm AX4318 Resist was dispensed onto the center of the wafer. The hood sash was closed and the wafer was spun at 3500 RPM for 25 seconds. After the spin-coater stopped, the wafer was

removed with wafer tweezers and put on a Thermolyne Type HP11500B Explosion Proof Hotplate for 60 seconds. The wafer was removed from the hotplate and allowed to cool for at least 10 minutes.

[0087] The film thickness of each wafer before dissolution was analyzed in three areas of the wafer and the results were recorded and averaged. The processed wafer was also visually examined to note any abnormalities. The photoresist-coated wafer was then placed in a Teflon® coated developer bath dish. A sample of each exemplary mixture was poured onto the wafer within the bath dish and the timer was started. After 10 minutes, the wafer was removed from the bath and rinsed with ultra high purity water or hexanes for sixty seconds. The front and back of each wafer was dried with a high-pressure nitrogen nozzle. The film thickness of each wafer after dissolution was analyzed in three areas and the results were recorded and averaged. The film thickness was also visually observed to note any abnormalities or changes, such as changes in color. In some instances, the results were independently verified using a quartz microbalance (QCM). The film thickness results are provided in Table IV.

[0088] Film thickness measurements for examples 19 through 28, which were mixtures containing acetylenic alcohols, acetylenic diols, co-solvents, or chelating agents of the present invention, illustrate that these mixtures removed at least 60.45%, and in the majority of the examples removed approximately 100%, of the 193 nm photoresist from the surface of the substrate. By contrast, examples 29 through 35 show that co-solvents used in the prior art are not as efficient at removing 193 nm photoresist at equivalent molar concentrations.

Table IV: Photoresist Dissolution and Stripping Studies Using Surrogate Solvents

Example	Entrainers	Molar % (wt %) Entrainer	% Resist Removal
19	Benzonitrile	10.01% (17.15%)	100%
20	Acetophenone	10.08% (13.53%)	100%
21	Amietol®E-21	10.05% (42.09%)	100%
22	Surfynol®61	10.15% (14.19%)	75.26%
23	Hydrogenated Surfynol®104	10.0% (22.89%)	100%
24	Dibutyl mallate	10.05% (24.22%)	100%
25	Hexafluoropropanol-acetylene	9.85% (19.42%)	86.48%
26	2-ethylaminoethanol	9.39% (33.90%)	70.84%
27a	Acetonitrile	10.01% (20.22%)	0
27b	Acetonitrile	25.10% (43.30%)	100%
28a	Propionitrile	10.05% (7.0%)	2.62%
28b	Propionitrile	19.19% (13.17%)	60.45%
29	Methanol	9.97% (16.44%)	< 1%
30	Acetic Acid	9.97% (26.97%)	< 1 %
31	Acetone	10.01% (26.38%)	0
32	Propylene Glycol	10.04% (32.04%)	< 2 %
33	n-methyl-pyrrolidinone (NMP)	10.0% (37.97%)	0
34	Dimethyl acetamide	10.06% (35.11%)	None
35	Ethyl acetate	10.02% (10.22%)	< 2%

Examples 36 through 55: Photoresist Stripping Test Results Using CO₂ as Dense Fluid and Acetylenic Alcohol and Diol-Based Formulations as Entrainers

- 5 **[0089]** The formulations shown in Table IV were used to remove Sumitomo AX-4138 (193 nm) photoresist from the surface of thermal-oxide coated (990 nm thickness), 4-inch wafers provided by University Wafers. The wafers were prime grade wafer N-type <100> wafers. They were prepared as follows: (a) the wafers were dried at ~250°C for 5 minutes under filtered nitrogen; (b) primed by exposing to HMDS vapor for 10 minutes at

ambient temperature; (c) photoresist was applied and then spun-coated to achieve ~400nm resist layer; (d) heated to 130°C for 2 minutes (note: since the wafers were not exposed on a lithography tool, the post exposure bake at 110°C was replaced by the hard bake conditions); (e) immersed in 0.26N TMAH developer solution for 60 seconds; 5 (f) rinsed with UPW and dry with filtered N₂; and (g) heated to 130°C for 2 minutes.

[0090] The thickness of the photoresist was measured before and after development. The results indicated that approximately 5 nm of resist was lost during the develop step (step (e) above). These wafers were blanket-etched to produce etched cross-linked photoresist. Five wafers were etched for 6.67 minutes and the remaining five wafers 10 were etched for 10 minutes, resulting in resist thickness losses of approximately 220 and 350 nm respectively. The wafers were then divided into 1-inch square pieces and the thickness of each piece measured at five different locations (four corners and the center) prior to cleaning. The resist thickness of the pieces etched for 6.67 minutes was approximately 180 nm; the resist thickness of the pieces etched for 10 minutes was 15 approximately 100 nm.

[0091] The pieces of etched wafers were then used in supercritical CO₂-based photoresist stripping tests. Process conditions and test results for several acetylenic alcohols and diols including Surfynol®420, Dynol®604, hydrogenated Surfynol®104, and Surfynol®61 with benzonitrile as a cosolvent are provided in Table V. Similar results 20 for propionitrile as a cosolvent are provided in Table VI. The CO₂ flow rate for all these cases was 1 liter/min. The entrainer represented 5-wt % of the dense cleaning fluid and comprised of an acetylenic alcohol, an acetylenic diol, a co-solvent (nitrile), or a mixture thereof. The co-solvent and/or acetylenic alcohol or diol were maintained in contact with the wafer for a total of four minutes soak time. After the soak was completed, the 25 process chamber was rapidly depressurized using a two step procedure in which the

pressure was decreased from 3300 psig to 1500 psig over a five second interval and then decreased from 1500 psig to atmospheric as fast as possible. The tests were conducted at a pressure of 3200 psig (~ 225 bar) and a temperature of 60°C. The wafers were rinsed in flowing supercritical CO₂ for 4 minutes subsequently to remove any traces of co-solvents and/or surfactant. The etched photoresist thickness was measured at five different locations on each wafer piece before and after exposing the wafer piece to the mixture containing supercritical CO₂, acetylenic alcohol or acetylenic diol, and/or co-solvent. A Filmetrics F20 Thin Film Measurement System was used to measure thickness.

5

10 **[0092]** The results show that formulations that comprise Surfynol®420, Dynol®604, hydrogenated Surfynol®104, and Surfynol®61 are particularly efficacious at removing etched photoresist. It was observed that photoresist and residue removal (as a percentage of the initial resist thickness) are relatively independent of initial thickness (etch time) and wafer position in the cleaning chamber. Although both co-solvents

15 (benzonitrile or propionitrile) remove resist partially (~ 80%), there is a substantial decrease in photoresist thickness and increase in cleaning efficiency when acetylenic alcohols or diols are added to either cosolvent, or when a chelating agent such as dibutyl

20 mixture containing Surfynol®420, any mixture containing hydrogenated Surfynol®104, and any mixture containing Dynol®604. By contrast, the dense fluid (supercritical CO₂) alone removed less than 16% of the photoresist.

Table V: Etched Photoresist Stripping Test Results with Supercritical CO₂, Benzonitrile, Acetylenic Alcohols and Diols, and Other Additives

Ex.	Co-solvent	Wt %	Entrainer	Wt %	Temp. (°C)	Press. (psig)	Contacting Mode	% Resist Removed
36	None	0.0	None	0.0	40.0	3300.0	Dynamic	11.6
37	None	0.0	None	0.0	60.0	3300.0	Dynamic	15.7
38	None	0.0	Surfynol®61	5.0	40.0	3300.0	Dynamic	50.
39	None	0.0	Surfynol®61	5.0	58.0	3274.0	Static	53.68
40	Benzonitrile	5.0	None	0.0	61.0	3215.0	Static	79.76
41	Benzonitrile	2.5	Surfynol®61	2.5	59.0	3215.0	Static	80.08
42	Benzonitrile	2.5	Surfynol®420	2.5	59.0	3215.0	Static	92.6
43a	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3220.0	Static	85.78
43b	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3220.0	Static	91.78
43c	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3220.0	Static	94.24
43d	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3220.0	Static	90.08
43e	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3220.0	Static	90.24
44	Benzonitrile	2.5	Surfynol®420	2.5	57.0	3191.0	Static	93.30
45	Benzonitrile	2.5	Dynol®604	2.5	57.0	3215.0	Static	91.83
46	Benzonitrile	2.5	Hydrogenated Surfynol®104	2.5	57.0	3191.0	Static	95.34
47	Benzonitrile	2.5	Dibutyl mallate	2.5	58.0	3220.0	Static	87.87

5 Table VI: Etched Photoresist Stripping Test Results with Supercritical CO₂, Propionitrile, Acetylenic Alcohols and Diols, and Other Additives

Ex.	Co-solvent	Wt %	Entrainer	Wt %	Temp. (°C)	Press. (psig)	Contacting Mode	% Resist Removed
48	Propionitrile	5.0	None	0.0	58.0	3222.0	Static	81.39
49	Propionitrile	2.5	Surfynol®61	2.5	58.0	3229.0	Static	95.23
50	Propionitrile	2.5	Surfynol®61	2.5	57.0	3191.0	Static	57.72
51	Propionitrile	2.5	Surfynol®61	2.5	57.0	3191.0	Static	86.40
52	Propionitrile	2.5	Surfynol®420	2.5	58.0	3220.4	Static	97.84
53	Propionitrile	2.5	Dynol®604	2.5	58.0	3220.4	Static	86.48
54	Propionitrile	2.5	Hydrogenated Surfynol®104	2.5	58.0	3234.9	Static	95.23
55	Propionitrile	2.5	Surfynol®420	2.5	57.0	3220.4	Static	94.15

[0093] The present invention has been set forth with regard to several preferred embodiments, but the scope of the present invention is considered to be broader than those embodiments and should be ascertained from the claims below.